



Cite this: *RSC Adv.*, 2017, 7, 9772

## Correction: A non-volatile resistive memory effect in 2,2',6,6'-tetraphenyl-dipyranylidene thin films as observed in field-effect transistors and by conductive atomic force microscopy

Marc Courté,<sup>a</sup> Sandeep G. Surya,<sup>b</sup> Ramesh Thamankar,<sup>c</sup> Chao Shen,<sup>a</sup>  
V. Ramgopal Rao,<sup>b</sup> Subodh G. Mhaisalkar<sup>de</sup> and Denis Fichou<sup>\*afg</sup>

DOI: 10.1039/c7ra90012k

[www.rsc.org/advances](http://www.rsc.org/advances)

Correction for 'A non-volatile resistive memory effect in 2,2',6,6'-tetraphenyl-dipyranylidene thin films as observed in field-effect transistors and by conductive atomic force microscopy' by Marc Courté *et al.*, *RSC Adv.*, 2017, 7, 3336–3342.

The authors regret that the name of the sixth author was presented incorrectly in the original article. Subodh G. Mhaisalkar's name has been corrected herein.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

<sup>a</sup>School of Physical and Mathematical Sciences, Nanyang Technological University, 637371, Singapore. E-mail: [denisfichou@ntu.edu.sg](mailto:denisfichou@ntu.edu.sg)

<sup>b</sup>Department of Electrical Engineering, Indian Institute of Technology Bombay, Mumbai 400 076, India

<sup>c</sup>School of Engineering and Technology, CMR University, Bangalore 560043, India

<sup>d</sup>School of Material Science and Engineering, Nanyang Technological University, 639798, Singapore

<sup>e</sup>Energy Research Institute@NTU (ERI@N), Nanyang Technological University, 637141, Singapore

<sup>f</sup>CNRS, UMR 8232, Institut Parisien de Chimie Moléculaire, F-75005, Paris, France

<sup>g</sup>Sorbonne Universités, UPMC Univ Paris 06, UMR 8232, Institut Parisien de Chimie Moléculaire, F-75005, Paris, France

